# **PNA1401L** (PN101)

### Silicon planar type

For optical control systems

#### ■ Features

- High sensitivity
- Wide spectral sensitivity characteristics, suited for detecting GaAs LEDs
- Low collector-emitter cutoff current (base open):  $I_{CEO} = 5 \text{ nA (typ.)}$
- Fast response:  $t_r$ ,  $t_f = 3 \mu s$  (typ.)
- TO-18 standard type package

#### ■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol	Rating	Unit	
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	30	V	
Emitter-collector voltage (Base open)	V <sub>ECO</sub>	5	V	
Collector current	$I_{C}$	50	mA	
Collector power dissipation *	P <sub>C</sub>	150	mW	
Operating ambient temperature	T <sub>opr</sub>	-25 to +85	°C	
Storage temperature	T <sub>stg</sub>	-30 to +100	°C	

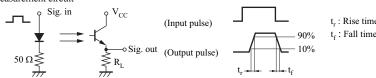
Note) \*: The rate of electric power reduction is 1.5 mW/ $^{\circ}$ C above  $T_a = 25 ^{\circ}$ C.

#### ■ Electrical-Optical Characteristics $T_a = 25$ °C±3°C

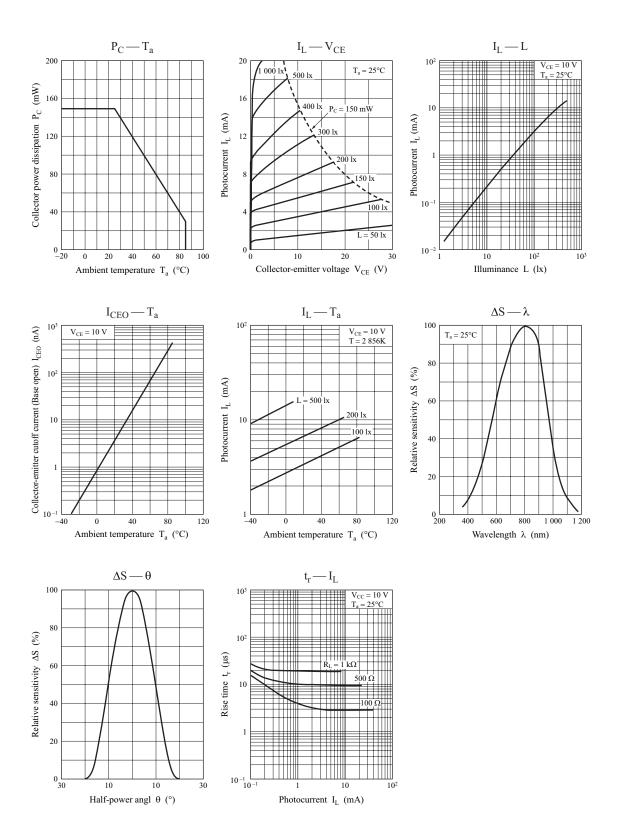
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Photocurrent *1	$I_{\rm L}$	$V_{CE} = 10 \text{ V}, L = 100 \text{ lx}$	1.5	3.5		mA
Collector-emitter cutoff current (Base open)	I <sub>CEO</sub>	$V_{CE} = 10 \text{ V}$		5	300	nA
Collector-emitter saturation voltage *1	V <sub>CE(sat)</sub>	$I_L = 1 \text{ mA}, L = 500 \text{ lx}$		0.2	0.4	V
Peak sensitivity wavelength	$\lambda_{\mathrm{PD}}$	$V_{CE} = 10 \text{ V}$		800		nm
Half-power angle	θ	The angle when the photocurrent is halved		10		0
Rise time *2	t <sub>r</sub>	V 10 V I 5 A D 100 O		3		μs
Fall time *2	$t_{\mathrm{f}}$	$V_{CC} = 10 \text{ V}, I_L = 5 \text{ mA}, R_L = 100 \Omega$		3		μs

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

- $2. \ \ Spectral \ sensitivity \ characteristics: Sensitivity \ for \ wave \ length \ over \ 400 \ nm \ maximum \ sensitivity \ ratio \ is \ 100\%.$
- 3. This device is designed by disregarding radiation.
- 4. \*1:Source: Tungsten lamp (color temperature 2 856K)
  - \*2: Switching time measurement circuit



Note) The part number in the parenthesis shows conventional part number.

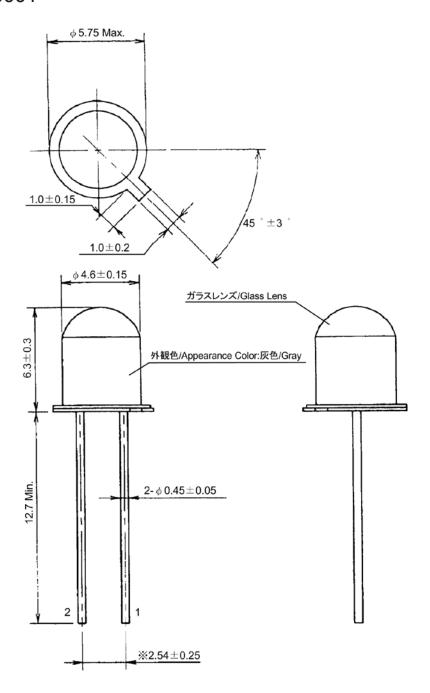


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Panasonic PNA1401L

■ Package (Unit: mm)

## MPCLTN2S0001



(注 1)※リード根元寸法とする。/(Note1)※Indicates root dimensions of lead. (注 2)マークは、目視又は顕微鏡において確認できる事。 (Notes2)What a mark sees an attention and can decode in a microscope.

- Pin name
  - 1: Emitter
- 2: Collector

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